#### **Thermal Characteristics**

| Package     | l <sub>D</sub><br>(continuous) <sup>†</sup><br>(mA) | l <sub>D</sub><br>(pulsed) <sup>†</sup><br>(A) | Power Dissipation<br>@T <sub>c</sub> = 25°C<br>(W) | θ <sub>ja</sub><br>(°C/W) | l <sub>DR</sub><br>(mA) | l <sub>DRM</sub> <sup>†</sup><br>(A) |  |
|-------------|---|--|--|---------------------------|-------------------------|--------------------------------------|--|
| 8-Lead SOIC | -700  | -1.25  | 1.5 <sup>‡</sup>                                   | 101 <sup>‡</sup>          | -700                    | -1.25                                |  |
| TO-92       | -500  | -1.25  | 1.0  | 132                       | -500                    | -1.25                                |  |

#### Notes:

- †  $I_{p}$  (continuous) is limited by max rated  $T_{p}$ .
- # Mounted on FR4 board, 25mm x 25mm x 1.57mm

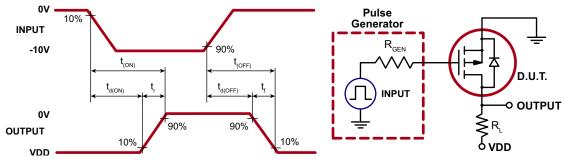
## **Electrical Characteristics** (T<sub>A</sub> = 25°C unless otherwise specified)

| Sym                 | Parameter                                      | Min   | Тур   | Max  | Units | Conditions   |
|---------------------|--|-------|-------|------|-------|--|
| BV <sub>DSS</sub>   | Drain-to-source breakdown voltage              | -16.5 | -     | -    | V     | $V_{GS} = 0V, I_{D} = -1.0 \text{mA}$                                |
| V <sub>GS</sub>     | Gate threshold voltage                         | -0.5  | -0.7  | -1.0 | V     | $V_{GS} = V_{DS}$ , $I_{D} = -1.0$ mA                                |
| $\Delta V_{GS(th)}$ | Change in V <sub>GS(th)</sub> with temperature | -     | -     | -4.0 | mV/°C | $V_{GS} = V_{DS}$ , $I_{D} = -1.0$ mA                                |
| I <sub>GSS</sub>    | Gate body leakage                              | -     | -     | -100 | nA    | $V_{GS} = \pm 10V, V_{DS} = 0V$                                      |
|                     |  | -     | -     | -100 | nA    | $V_{DS} = -15V, V_{GS} = 0V$   |
| l <sub>DSS</sub>    | Zero gate voltage drain current                | -     | -     | -1.0 | mA    | $V_{DS} = 0.8$ Max Rating,<br>$V_{GS} = 0V$ , $T_{A} = 125^{\circ}C$ |
|                     |  | -     | -0.4  | -    |       | $V_{GS} = V_{DS} = -2.0V$  |
| I <sub>D(ON)</sub>  | On-state drain current                         | -0.6  | -1.0  | -    | Α     | $V_{GS} = V_{DS} = -3.0V$  |
|                     |  | -1.25 | -2.30 | -    |       | $V_{GS} = V_{DS} = -5.0V$  |
|                     |  | -     | 2.0   | 4.0  | Ω     | $V_{GS} = -2.0V, I_{D} = -50mA$                                      |
| R <sub>DS(ON)</sub> | Static drain-to-source on-state resistance     | -     | 1.7   | 2.0  |       | $V_{GS} = -3.0V, I_{D} = -150mA$                                     |
| , ,                 | resistance                                     | -     | 1.3   | 1.5  |       | $V_{GS} = -5.0V, I_{D} = -300mA$                                     |
| $\Delta R_{DS(ON)}$ | Change in R <sub>DS(ON)</sub> with temperature | -     | -     | 0.75 | %/°C  | $V_{GS} = -5.0V, I_{D} = -300mA$                                     |
| G <sub>FS</sub>     | Forward transconductance                       | 500   | 700   | -    | mmho  | $V_{GS} = -15V, I_{D} = -1.0A$                                       |
| C <sub>ISS</sub>    | Input capacitance                              | -     | 120   | 250  | pF    | $V_{GS} = 0V$ ,  |
| C <sub>oss</sub>    | Common source output capacitance               | -     | 100   | 125  |       | $V_{DS} = -15V,$   |
| C <sub>RSS</sub>    | Reverse transfer capacitance                   | -     | 40    | 60   |       | f = 1.0MHz   |
| t <sub>d(ON)</sub>  | Turn-on delay time                             | -     | -     | 20   |       |  |
| t <sub>r</sub>      | Rise time                                      | -     | -     | 20   |       | $V_{DD} = -15V,$<br>$I_{D} = -1.25A,$                                |
| t <sub>d(OFF)</sub> | Turn-off delay time                            | -     | -     | 30   | ns    | $R_{GEN} = 25\Omega$   |
| t <sub>f</sub>      | Fall time                                      | -     | -     | 30   |       | GEN - 5  |
| V <sub>SD</sub>     | Diode forward voltage drop                     | -     | -1.2  | -1.5 | V     | $V_{GS} = 0V, I_{SD} = -500 \text{mA}$                               |

#### Notes:

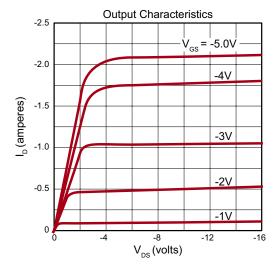
- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
  All A.C. parameters sample tested.

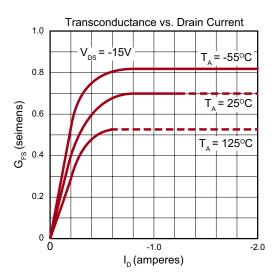
### **Switching Waveforms and Test Circuit**

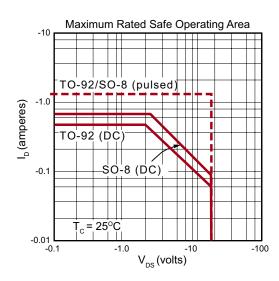


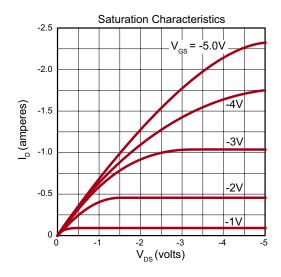
Supertex inc. www.supertex.com

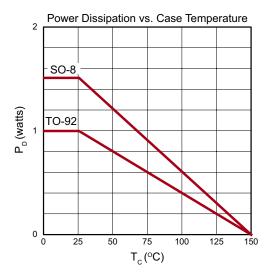
## **Typical Performance Curves**

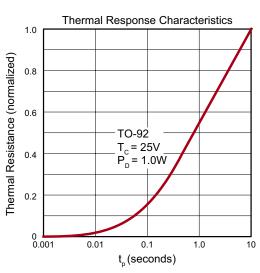




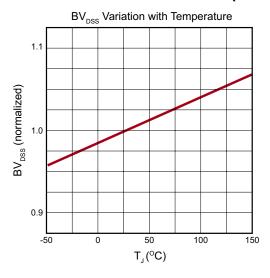


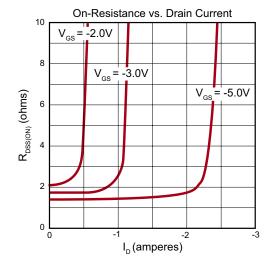


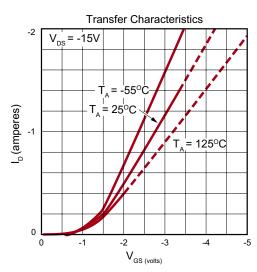


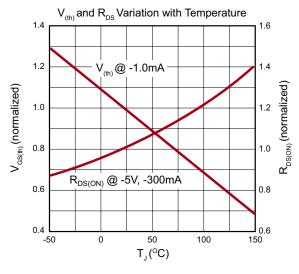


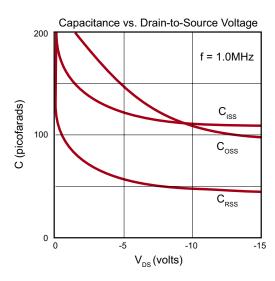
### **Typical Performance Curves (cont.)**

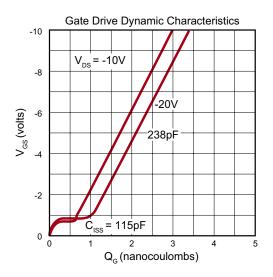




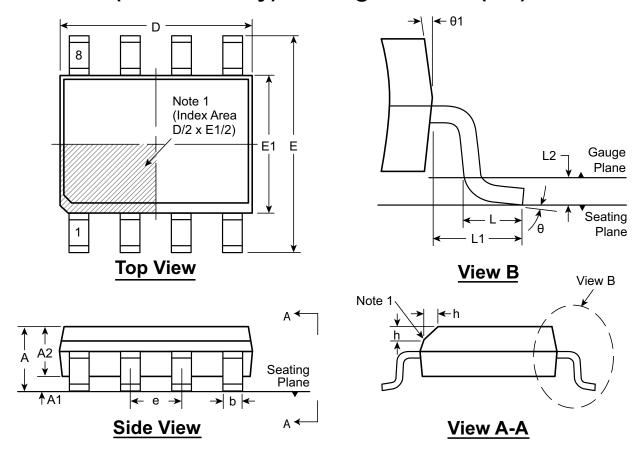








# 8-Lead SOIC (Narrow Body) Package Outline (LG)



#### Note:

1. This chamfer feature is optional. A Pin 1 identifier must be located in the index area indicated. The Pin 1 identifier can be: a molded mark/identifier; an embedded metal marker; or a printed indicator.

| Symbol         |     | Α     | A1   | A2    | b    | D     | E     | E1    | е             | h    | L    | L1          | L2 | θ          | θ1  |
|----------------|-----|-------|------|-------|------|-------|-------|-------|---------------|------|------|-------------|----|------------|-----|
| Dimension (mm) | MIN | 1.35* | 0.10 | 1.25  | 0.31 | 4.80* | 5.80* | 3.80* | 1.27<br>BSC - | 0.25 | 0.40 |             |    | <b>0</b> o | 5°  |
|                | NOM | -     | -    | -     | -    | 4.90  | 6.00  | 3.90  |               | -    |      | 0.25<br>BSC | -  | -          |     |
|                | MAX | 1.75  | 0.25 | 1.65* | 0.51 | 5.00* | 6.20* | 4.00* |               | 0.50 | 1.27 |             |    | <b>8</b> º | 15° |

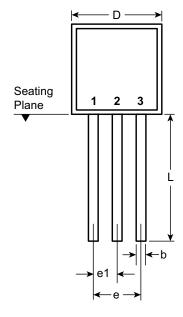
JEDEC Registration MS-012, Variation AA, Issue E, Sept. 2005.

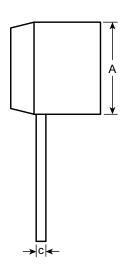
Drawings are not to scale.

Supertex Doc. #: DSPD-8SOLGTG, Version 1041309.

<sup>\*</sup> This dimension is not specified in the JEDEC drawing.

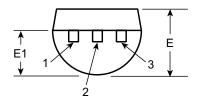
## 3-Lead TO-92 Package Outline (N3)





Front View

Side View



**Bottom View** 

| Symbol                 |     | Α    | b                 | С                 | D    | E    | E1   | е    | e1   | L     |
|------------------------|-----|------|-------------------|-------------------|------|------|------|------|------|-------|
| Dimensions<br>(inches) | MIN | .170 | .014 <sup>†</sup> | .014 <sup>†</sup> | .175 | .125 | .080 | .095 | .045 | .500  |
|                        | NOM | -    | -                 | -                 | -    | -    | -    | -    | -    | -     |
|                        | MAX | .210 | .022 <sup>†</sup> | .022 <sup>†</sup> | .205 | .165 | .105 | .105 | .055 | .610* |

JEDEC Registration TO-92.

Drawings not to scale.

Supertex Doc.#: DSPD-3TO92N3, Version E041009.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to <a href="http://www.supertex.com/packaging.html">http://www.supertex.com/packaging.html</a>.)

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<sup>\*</sup> This dimension is not specified in the JEDEC drawing.

<sup>†</sup> This dimension differs from the JEDEC drawing.